



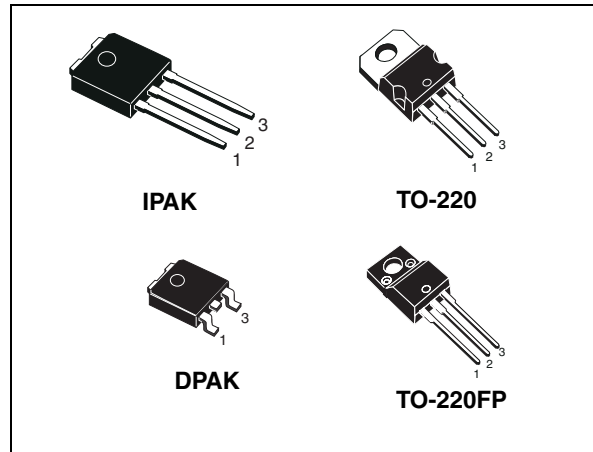
STD7NM60N, STF7NM60N STP7NM60N, STU7NM60N

N-channel 600 V, 5 A, 0.84 Ω DPAK, TO-220FP, TO-220, IPAK
second generation MDmesh™ Power MOSFET

Features

Order codes	V_{DS} @ T_{Jmax}	$R_{DS(on)}$ max.	I_D
STD7NM60N STF7NM60N STP7NM60N STU7NM60N	650 V	< 0.9 Ω	5 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



Application

Switching applications

Description

These devices are N-channel Power MOSFETs realized using the second generation of MDmesh™ technology. It applies the benefits of the multiple drain process to STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product offers improved on-resistance, low gate charge, high dv/dt capability and excellent avalanche characteristics.

Figure 1. Internal schematic diagram

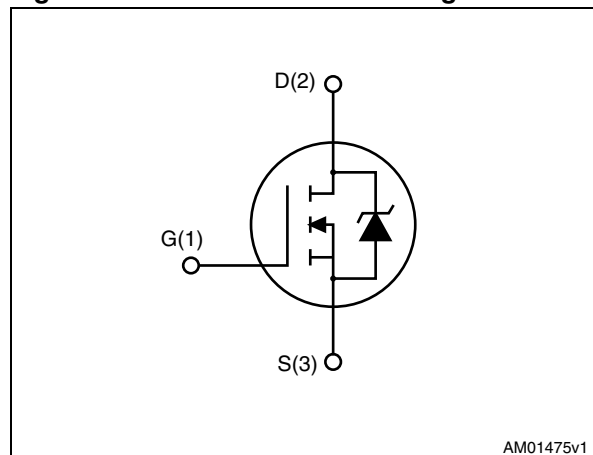


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD7NM60N	7NM60N	DPAK	Tape and reel
STF7NM60N		TO-220FP	Tube
STP7NM60N		TO-220	Tube
STU7NM60N		IPAK	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220, IPAK, DPAK	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	600		V
V_{GS}	Gate-source voltage	± 25		V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	5	5 ⁽¹⁾	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	3	3 ⁽¹⁾	A
$I_{DM}^{(2)}$	Drain current (pulsed)	20	20 ⁽¹⁾	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	45	20	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15		V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}$; $T_C = 25\text{ }^{\circ}\text{C}$)	2500		V
T_{stg}	Storage temperature	- 55 to 150		$^{\circ}\text{C}$
T_j	Max. operating junction temperature	150		$^{\circ}\text{C}$

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{Peak} < V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value				Unit
		DPAK	IPAK	TO-220	TO-220FP	
R _{thj-case}	Thermal resistance junction-case max	2.78			6.25	°C/W
R _{thj-amb}	Thermal resistance junction-ambient max		100	62.5		°C/W
R _{thj-pcb}	Thermal resistance junction-pcb max	50				°C/W
T _l	Maximum lead temperature for soldering purpose		300			°C

Table 4. Thermal data

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	2	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	119	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	600			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 2.5\text{ A}$		0.84	0.9	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	363 24.6 1.1	-	pF pF pF
$C_{oss\text{ eq.}}^{(1)}$	Output equivalent capacitance	$V_{DS} = 0\text{ to }480\text{ V}$, $V_{GS} = 0$	-	130	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	5.4	-	Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480\text{ V}$, $I_D = 5\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 18)	-	14 2.7 7.7	-	nC nC nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS} .

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 2.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 19)	-	7	-	ns
t_r	Rise time			10		ns
$t_{d(off)}$	Turn-off-delay time			26		ns
t_f	Fall time			12		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				20	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 5\text{ A}$, $V_{GS} = 0$	-		1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 22)	-	213		ns
Q_{rr}	Reverse recovery charge			1.5		nC
I_{RRM}	Reverse recovery current			14		A
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 22)	-	265		ns
Q_{rr}	Reverse recovery charge			1.8		nC
I_{RRM}	Reverse recovery current			14		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for DPAK, IPAK Figure 3. Thermal impedance for DPAK, IPAK

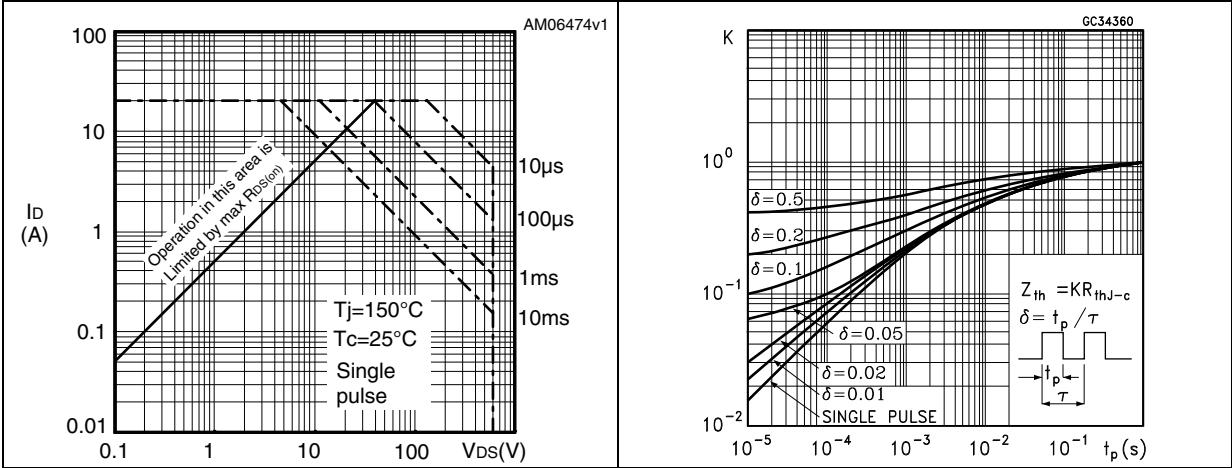


Figure 4. Safe operating area for TO-220FP Figure 5. Thermal impedance for TO-220FP

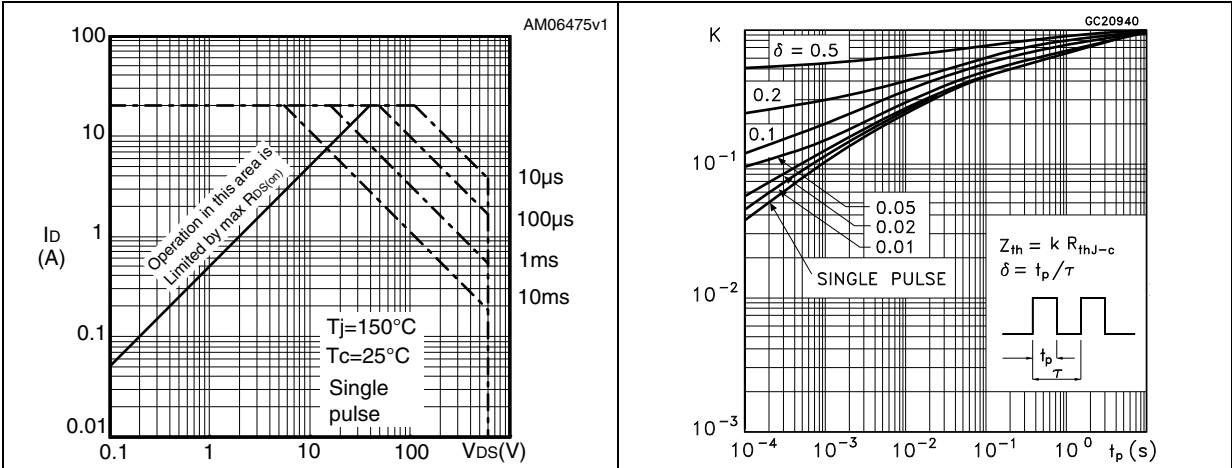


Figure 6. Safe operating area for TO-220 Figure 7. Thermal impedance for TO-220

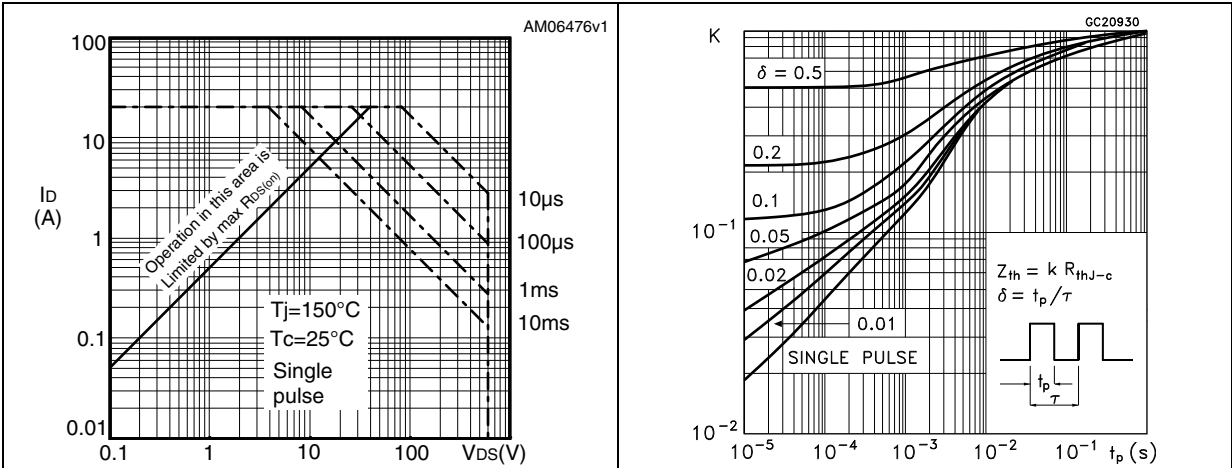


Figure 8. Output characteristics

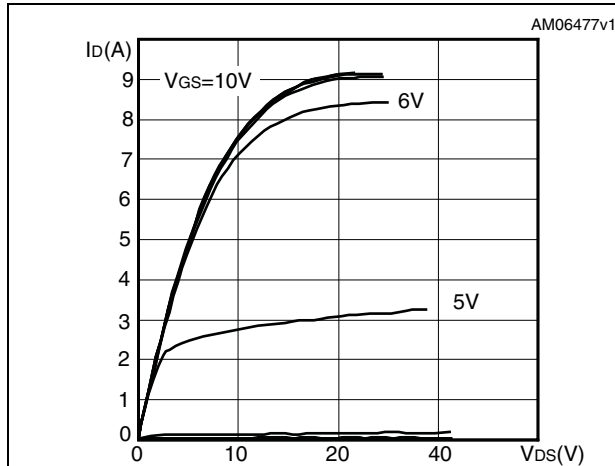


Figure 9. Transfer characteristics

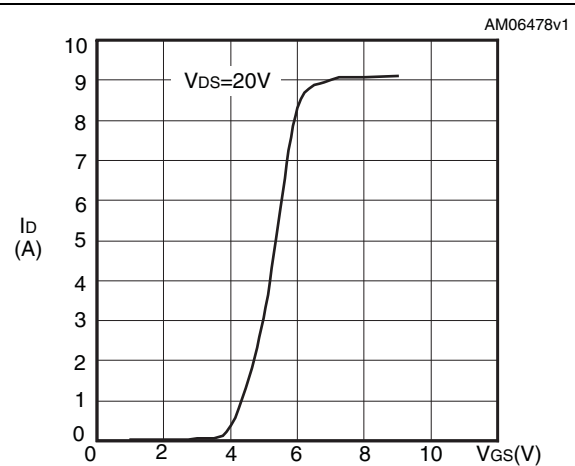


Figure 10. Gate charge vs gate-source voltage

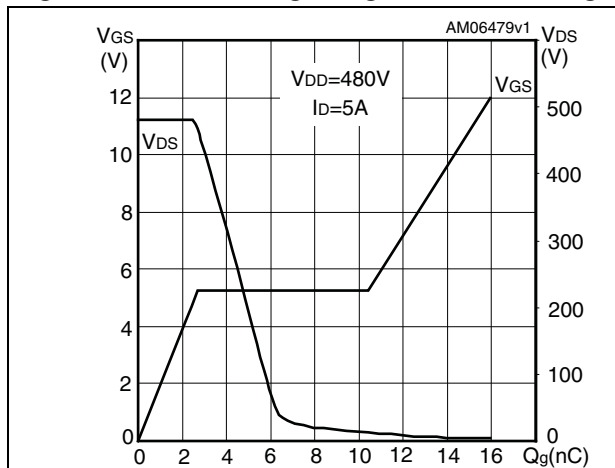


Figure 11. Static drain-source on resistance

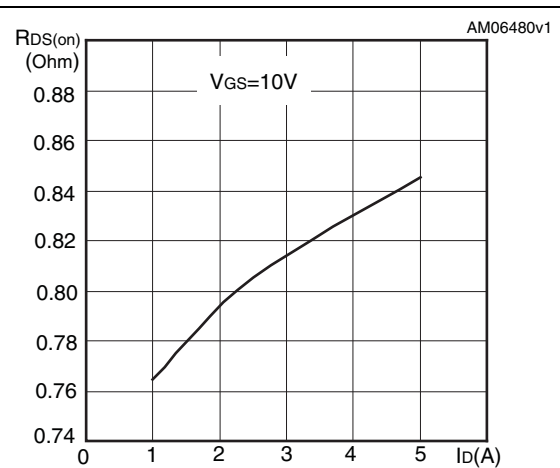


Figure 12. Capacitance variations

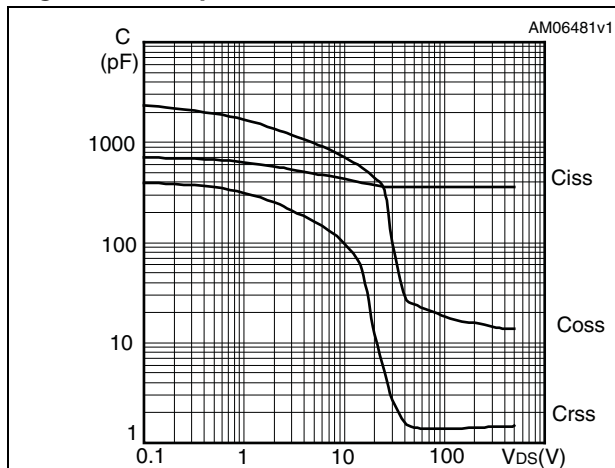


Figure 13. Output capacitance stored energy

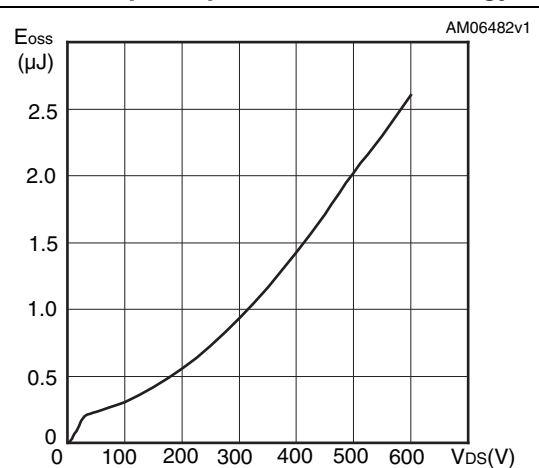


Figure 14. Normalized gate threshold voltage vs temperature

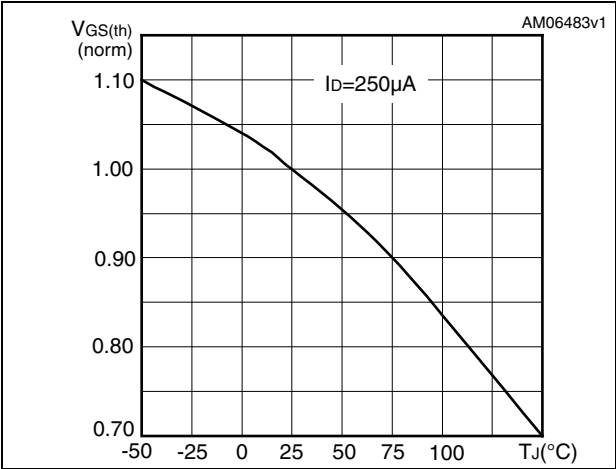


Figure 15. Normalized on resistance vs temperature

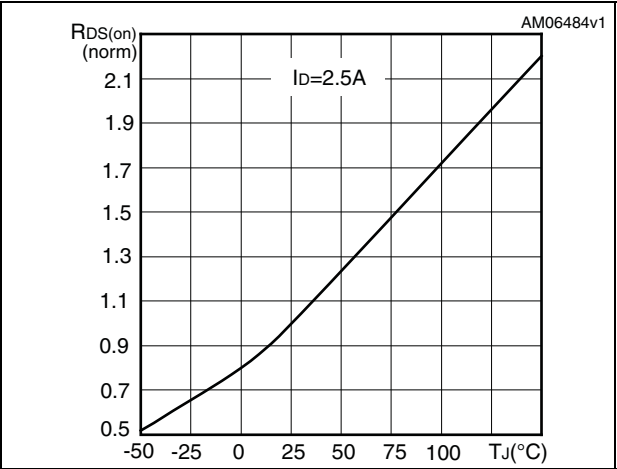
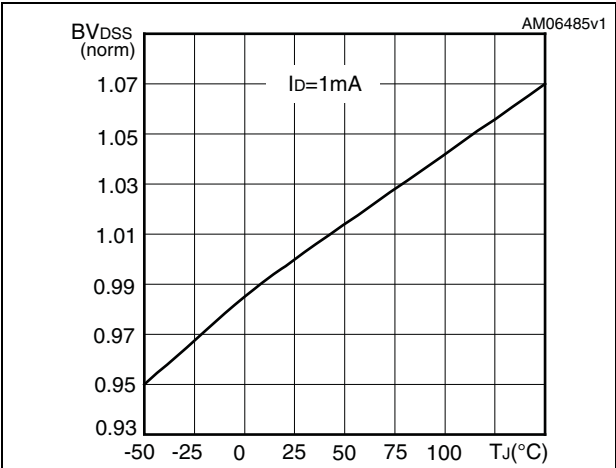


Figure 16. Normalized B_{VDSS} vs temperature



3 Test circuits

Figure 17. Switching times test circuit for resistive load



Figure 18. Gate charge test circuit



Figure 19. Test circuit for inductive load switching and diode recovery times

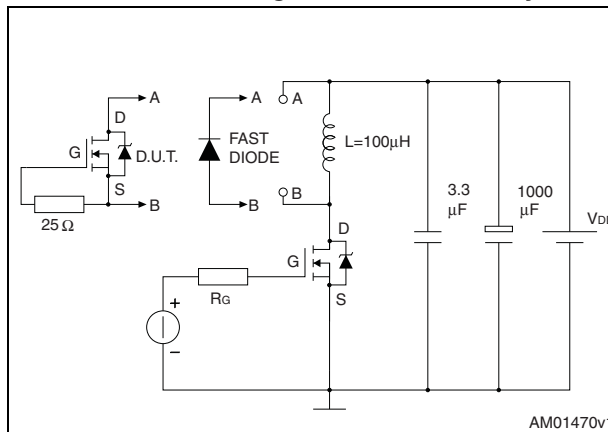


Figure 20. Unclamped inductive load test circuit



Figure 21. Unclamped inductive waveform

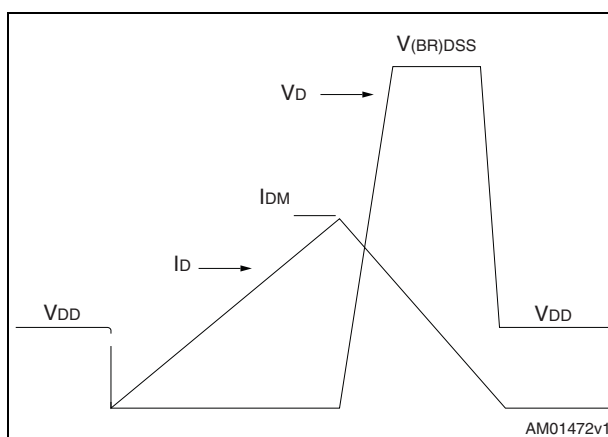
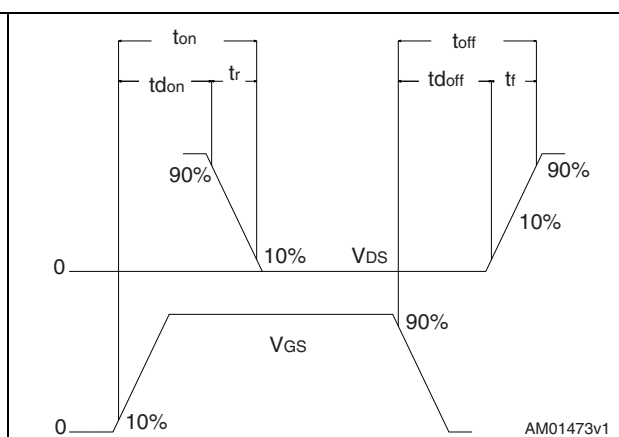


Figure 22. Switching time waveform



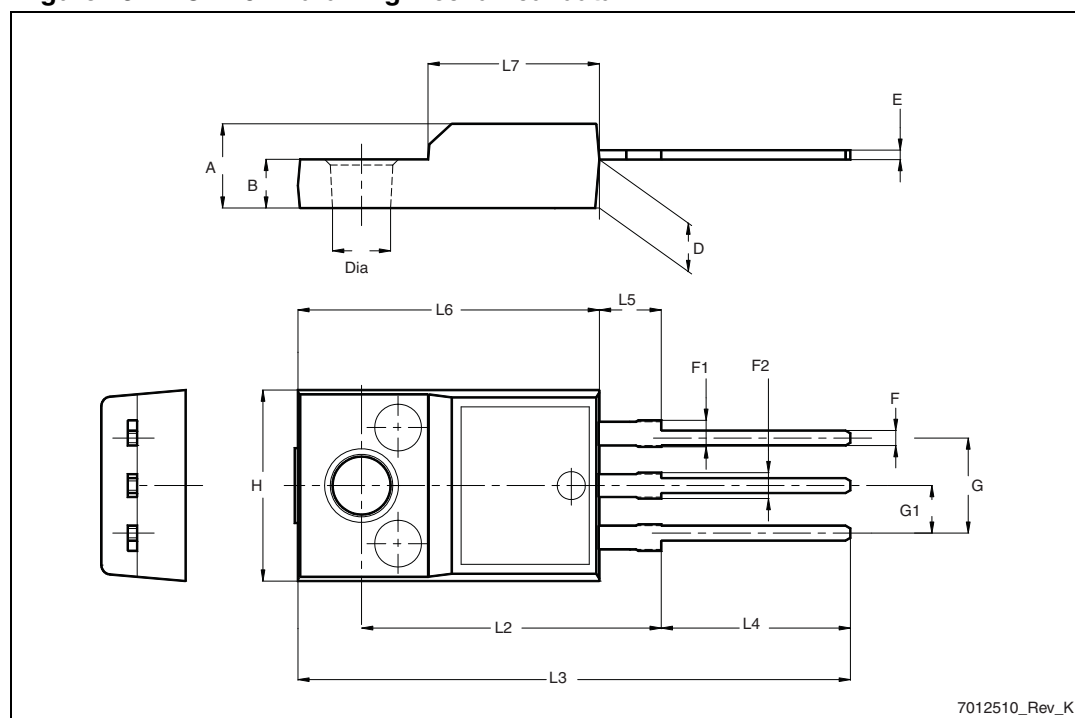
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. TO-220FP mechanical data

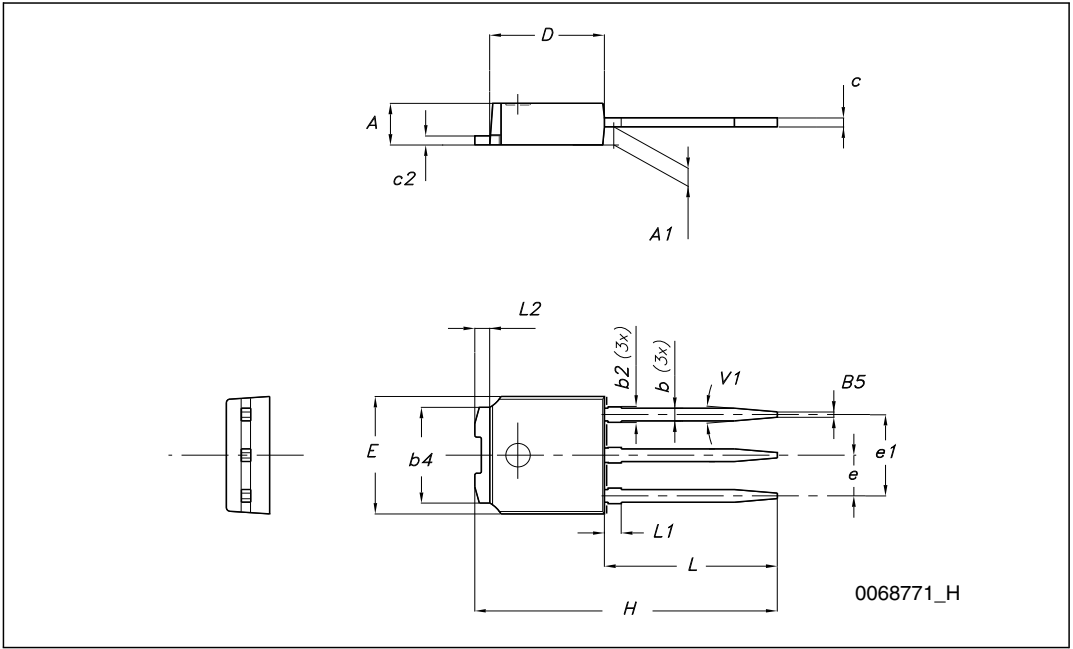
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 23. TO-220FP drawing mechanical data



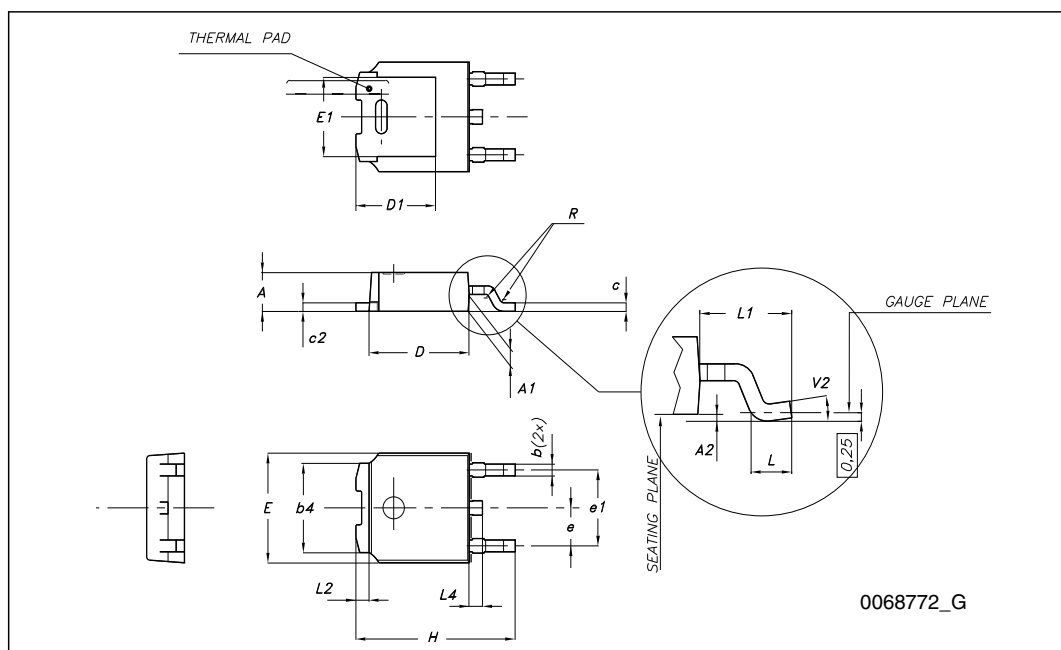
TO-251 (IPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10 °	



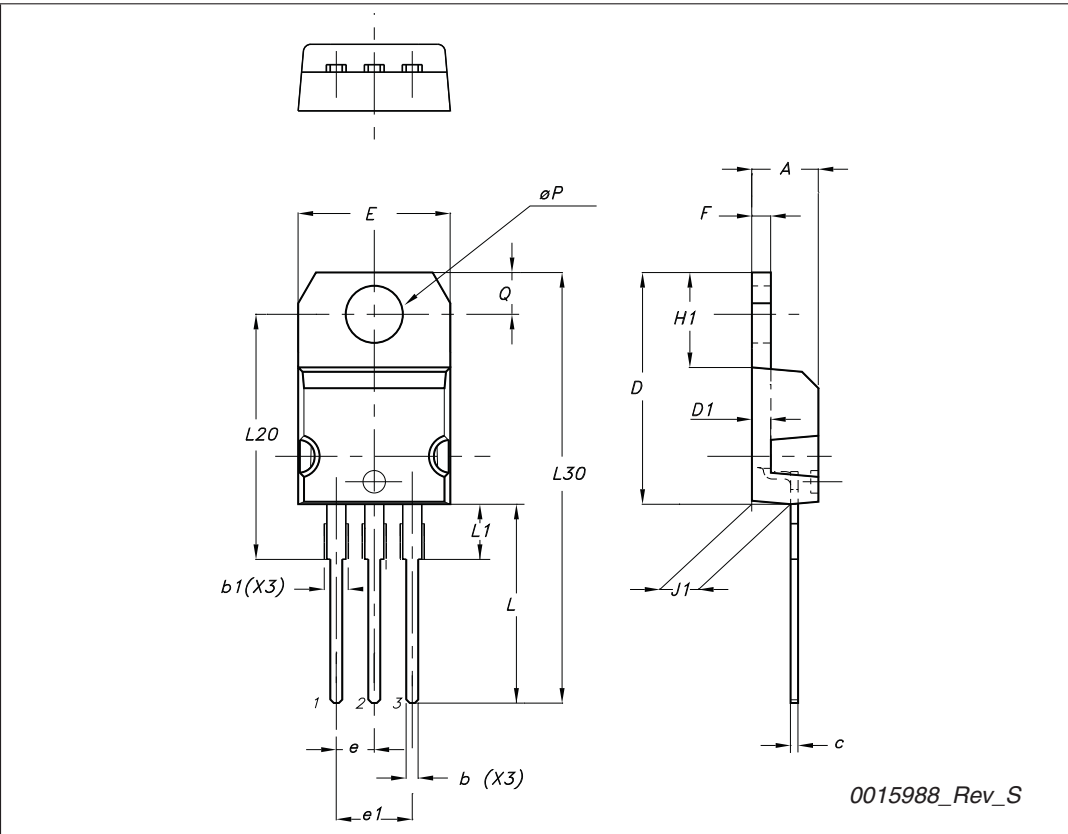
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0 °		8 °



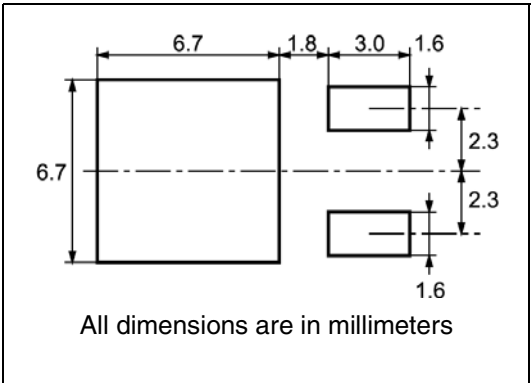
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

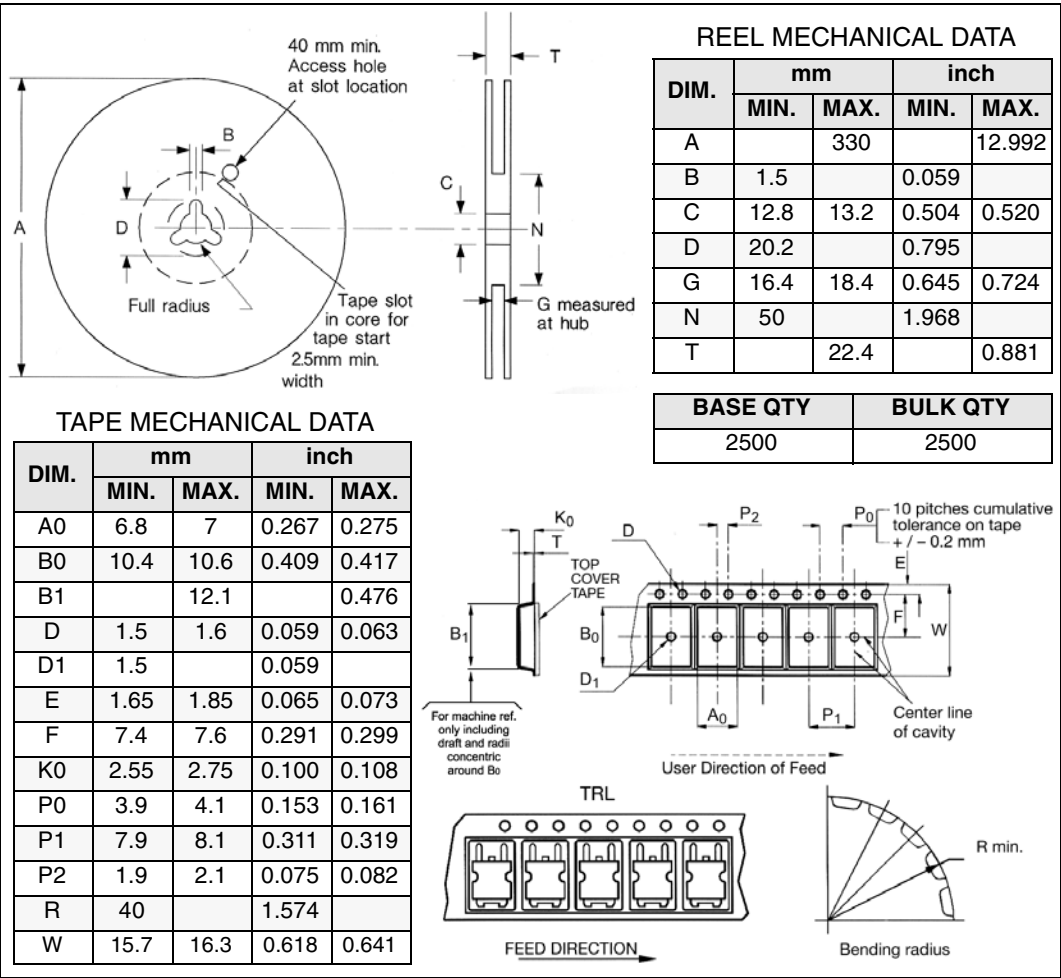


5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



6 Revision history

Table 10. Document revision history

Date	Revision	Changes
29-Oct-2009	1	First release.
19-Jul-2010	2	Corrected values in Table 3: Thermal data .
11-Oct-2010	3	Inserted new value in Table 6: Dynamic
04-Nov-2010	4	Changed $R_{DS(on)}$ typical value.

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